

# SANYO Semiconductors

## DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

# ATP214 — General-Purpose Switching Device Applications

### **Features**

- ON-resistance RDS(on)1=6.2m $\Omega$ (typ.)
- 4V drive
- · Protection diode in

- Input Capacitance Ciss=4850pF(typ.)
- · Halogen free compliance

### **Specifications**

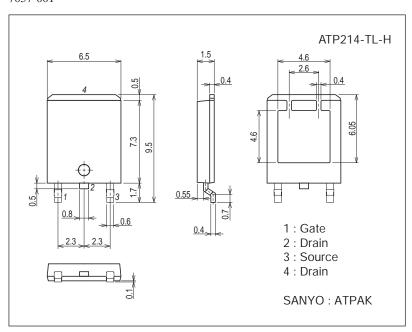
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		60	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		75	А
Drain Current (PW≤10μs)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	225	А
Allowable Power Dissipation	PD	Tc=25°C	60	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		94	mJ
Avalanche Current *2	I <sub>AV</sub>		38	А

Note :\*1 VDD=15V, L=100 $\mu$ H, IAV=38A

### **Package Dimensions**

unit : mm (typ) 7057-001



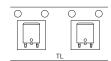
### **Product & Package Information**

• Package : ATPAK

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

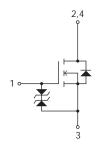
### Packing Type: TL



### Marking



### **Electrical Connection**

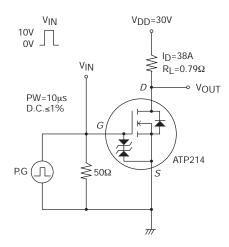


<sup>\*2</sup> L≤100µH, Single pulse

### Electrical Characteristics at Ta=25°C

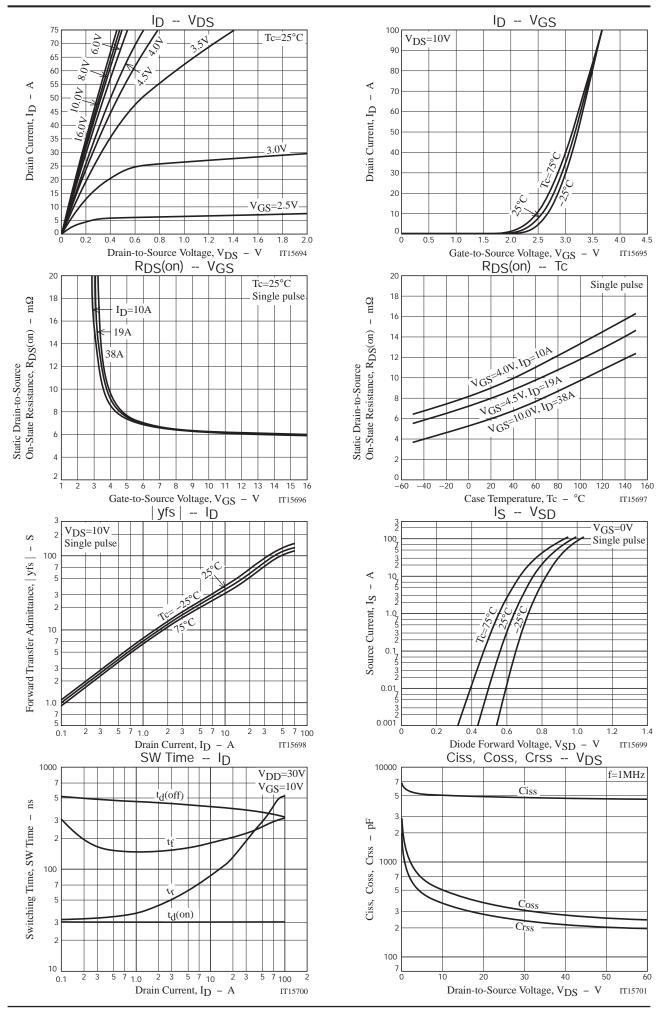
Parameter	Cumbal	Conditions	ano.	Ratings		- Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	60			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V	
Forward Transfer Admittance	yfs	VDS=10V, ID=38A		100		S	
	R <sub>DS</sub> (on)1	I <sub>D</sub> =38A, V <sub>G</sub> S=10V		6.2	8.1	mΩ	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =19A, V <sub>G</sub> S=4.5V		8.2	11.5	mΩ	
	R <sub>DS</sub> (on)3	I <sub>D</sub> =10A, V <sub>G</sub> S=4V		9.2	14	mΩ	
Input Capacitance	Ciss			4850		pF	
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		370		pF	
Reverse Transfer Capacitance	Crss			280		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			30		ns	
Rise Time	t <sub>r</sub>	Constant Total Circuit		240		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		360		ns	
Fall Time	tf			250		ns	
Total Gate Charge	Qg			96		nC	
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =75A		18.5		nC	
Gate-to-Drain "Miller" Charge	Qgd			18		nC	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =75A, V <sub>GS</sub> =0V		0.93	1.2	V	

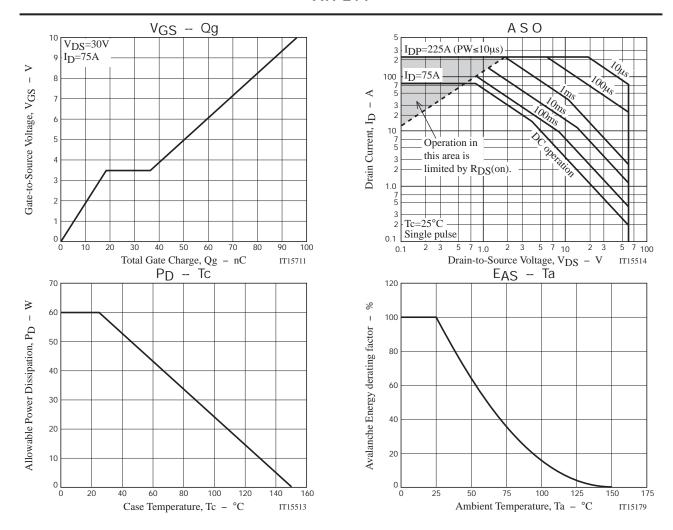
### Switching Time Test Circuit



### **Ordering Information**

Device	Package Shipping		memo	
ATP214-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free	



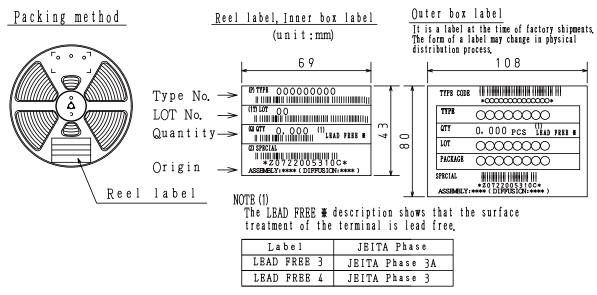


### **Taping Specification**

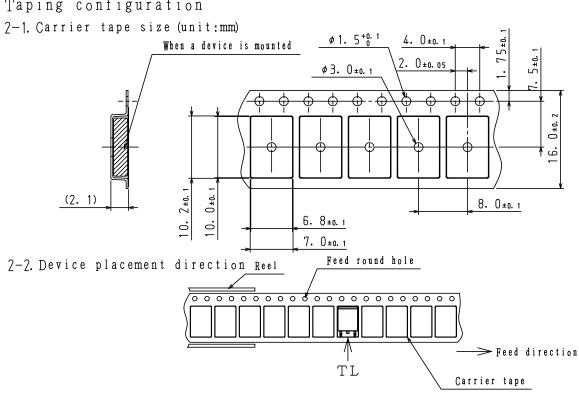
ATP214-TL-H

### 1. Packing Format (TL)

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
Lacyake Mame	Туре	Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18	
					1 reels contained	5 inner boxes contained	
ATPAK ATP 3	3,000 3,	3,000	15,000	Dimensions:mm (external)	Dimensions:mm (external)		
					340×340×28	355×355×165	



### 7. Taping configuration



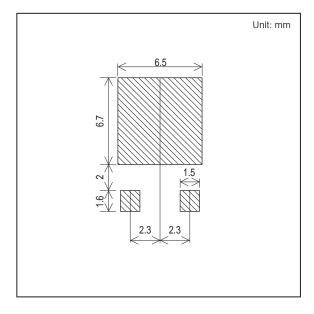
The one erectrode terminals on feed hole side····TL

### **Outline Drawing**

ATP214-TL-H

# Mass (g) Unit 0.266 For reference mm 6.540.15 2.520.15 3.520.15 3.520.15 3.520.15 4.520.15

### **Land Pattern Example**



Note on usage: Since the ATP214 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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